

(Supplemental Document)

Enhancement of Ferroelectric Phase Formation of HfO₂/ZrO₂ Nanolaminate Films by Tuning HfO₂ and ZrO₂ Thicknesses Using Atomic Layer Deposition

Takashi Onaya et al.

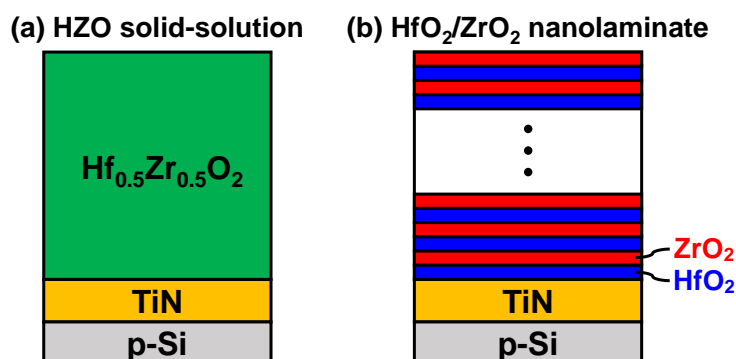


Fig. 1 Schematic illustrations of (a) Hf_xZr_{1-x}O₂ (HZO) solid-solution and (b) HfO₂/ZrO₂ nanolaminate films with the thickness of 10 nm fabricated on TiN/p-Si substrates. A 10-nm-thick HZO solid-solution film was deposited by atomic layer deposition (ALD) at 300°C using a Hf/Zr[N(C₂H₅)CH₃]₄ cocktail precursor and H₂O. A 10-nm-thick HfO₂/ZrO₂ nanolaminate film was deposited by alternately depositing HfO₂ and ZrO₂ layers using ALD at 300°C. HfO₂ and ZrO₂ layers were deposited using Hf[N(C₂H₅)CH₃]₄ and Zr[N(C₂H₅)CH₃]₄ precursors, respectively, and H₂O as an oxidant. The ALD growth rates of HfO₂ and ZrO₂ were almost the same of ~0.08 nm/cycle. The Hf:Zr ratios in HZO solid-solution and HfO₂/ZrO₂ nanolaminate films were 1:1. For HfO₂/ZrO₂ nanolaminate films, the ALD cycle ratio was varied from HfO₂/ZrO₂=1/1 to 60/60 so that each HfO₂ and ZrO₂ thickness would be varied from 0.08 to 5 nm while keeping the same thickness of HfO₂ and ZrO₂ layers.

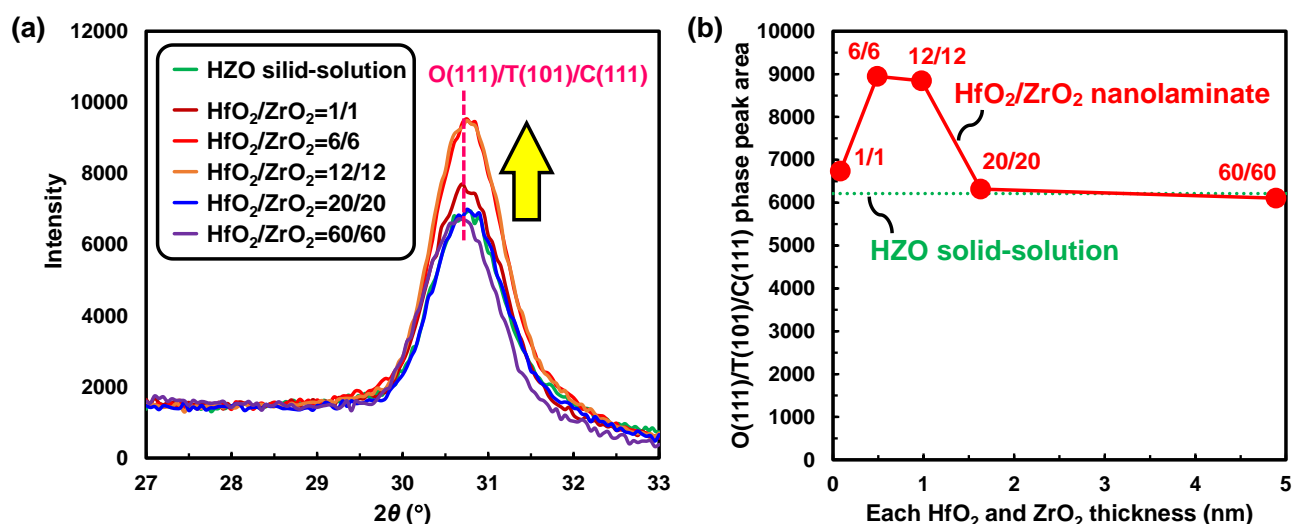


Fig. 2 (a) Grazing-incidence X-ray diffraction (GIXRD) spectra and (b) peak areas of orthorhombic (O) (111), tetragonal (T) (101), and cubic (C) (111) phases for HZO solid-solution and HfO₂/ZrO₂ nanolaminate films after the post-deposition annealing at 600°C. The HfO₂/ZrO₂=1/1 and HZO solid-solution films exhibited similar O/T/C peak area, because Hf and Zr atoms could be uniformly mixed in the HfO₂/ZrO₂=1/1 film. On the other hand, the O/T/C peak areas of the HfO₂/ZrO₂=6/6 and 12/12 films were ~1.4 times larger than that of the HZO solid-solution film, where each HfO₂ and ZrO₂ thickness was 0.5–1 nm (1–2 monolayers). Therefore, the ZrO₂ layers in HfO₂/ZrO₂ nanolaminate films should play a role to provide nuclei efficiently to enhance the formation of O/T/C phases in the HfO₂/ZrO₂=6/6 and 12/12 films.